

# Soyoun Kim

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Investigation of Electrical Characteristic Behavior Induced by Channel-Release Process in Stacked Nanosheet Gate-All-Around MOSFETs. IEEE Transactions on Electron Devices, 2020, 67, 2648-2652.	3.0	31
2	Surface Ge-rich p-type SiGe channel tunnel field-effect transistor fabricated by local condensation technique. Solid-State Electronics, 2020, 164, 107701.	1.4	13
3	Investigation of Device Performance for Fin Angle Optimization in FinFET and Gate-All-Around FETs for 3 nm-Node and Beyond. IEEE Transactions on Electron Devices, 2022, 69, 2088-2093.	3.0	11
4	Vertically-Stacked Si <sub>0.2</sub> Ge <sub>0.8</sub> Nanosheet Tunnel FET With 70 mV/Dec Average Subthreshold Swing. IEEE Electron Device Letters, 2021, 42, 962-965.	3.9	4
5	Sub-10 nm advanced finfet design for different applications in various vdd and temperature operation ranges. , 2019, , .		1
6	Local Variation-Aware Transistor Design through Comprehensive Analysis of Various Vdd/Temperatures using Sub-7nm Advanced FinFET Technology. , 2020, , .		1
7	Novel Stacked Floating Fin Structure Gate-All-Around Field-Effect Transistor for Design and Power Optimization. , 2019, , .		0
8	Accurate Effective Width Extraction Methods for Sub-10nm Multi-Gate MOSFETs through Capacitance Measurement. , 2019, , .		0
9	I-Shaped SiGe Fin Tunnel Field-Effect Transistor with High ION/IOFF Ratio. Journal of Nanoscience and Nanotechnology, 2020, 20, 4298-4302.	0.9	0